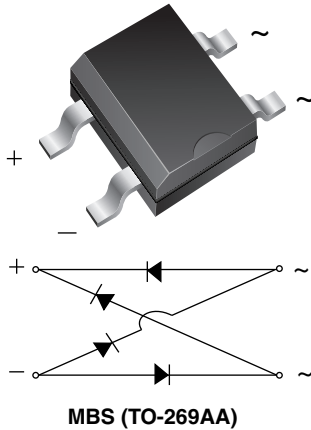


Miniature Glass Passivated Fast Recovery Surface-Mount Bridge Rectifier



FEATURES

- UL recognition, file number E54214
- Saves space on printed circuit boards
- Ideal for automated placement
- High surge current capability
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Material categorization: for definitions of compliance please see



TYPICAL APPLICATIONS

General purpose use in AC/DC bridge full wave rectification for power supply, lighting ballaster, battery charger, home appliances, office equipment, and telecommunication applications.

LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS	
$I_{F(AV)}$	0.5 A
V_{RRM}	200 V, 400 V, 600 V
I_{FSM}	35 A
I_R	5 μ A
V_F at $I_F = 0.4$ A	1.0 V
T_J max.	150 °C
Package	MBS (TO-269AA)
Circuit configuration	Quad

MECHANICAL DATA

Case: MBS (TO-269AA)

Molding compound meets UL 94 V-0 flammability rating
Base P/N-E3 - RoHS-compliant, commercial grade

Terminals: matte tin plated leads, solderable per J-STD-002 and JESD22-B102

E3 suffix meets JESD 201 class 1A whisker test

Polarity: as marked on body

MAXIMUM RATINGS (T _A = 25 °C unless otherwise noted)					
PARAMETER	SYMBOL	MB2S	MB4S	MB6S	UNIT
Device marking code		2	4	6	
Maximum repetitive peak reverse voltage	V _{RRM}	200	400	600	V
Maximum RMS voltage	V _{RMS}	140	280	420	V
Maximum DC blocking voltage	V _{DC}	200	400	600	V
Maximum average forward output rectified current (fig. 1)	I _{F(AV)}	0.5			A
on glass-epoxy PCB ⁽¹⁾ on aluminum substrate ⁽²⁾		0.8			
Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load	I _{FSM}	35			A
Rating for fusing (t < 8.3 ms)	I²t	5.0			A²s
Operating junction and storage temperature range	T _J , T _{STG}	-55 to +150			°C

Notes

⁽¹⁾ On glass epoxy PCB mounted on 0.05" x 0.05" (1.3 mm x 1.3 mm) pads

⁽²⁾ On aluminum substrate PCB with an area of 0.8" x 0.8" (20 mm x 20 mm) mounted on 0.05" x 0.05" (1.3 mm x 1.3 mm) solder pad

ELECTRICAL CHARACTERISTICS (T _A = 25 °C unless otherwise noted)						
PARAMETER	TEST CONDITIONS	SYMBOL	MB2S	MB4S	MB6S	UNIT
Maximum instantaneous forward voltage per diode	I _F = 0.4 A	V _F	1.0			V
Maximum DC reverse current at rated DC blocking voltage per diode	T _A = 25 °C	I _R	5.0			μA
	T _A = 125 °C		100			
Typical junction capacitance per diode	4.0 V, 1 MHz	C _J	13			pF

THERMAL CHARACTERISTICS (T _A = 25 °C unless otherwise noted)					
PARAMETER	SYMBOL	MB2S	MB4S	MB6S	UNIT
Typical thermal resistance	R _{θJA} ⁽¹⁾	85			°C/W
	R _{θJA} ⁽²⁾	70			
	R _{θJL} ⁽¹⁾	20			

Notes
⁽¹⁾ On glass epoxy PCB mounted on 0.05" x 0.05" (1.3 mm x 1.3 mm) pads

⁽²⁾ On aluminum substrate PCB with an area of 0.8" x 0.8" (20 mm x 20 mm) mounted on 0.05" x 0.05" (1.3 mm x 1.3 mm) solder pad

ORDERING INFORMATION (Example)				
PREFERRED P/N	UNIT WEIGHT (g)	PREFERRED PACKAGE CODE	BASE QUANTITY	DELIVERY MODE
MB2S-E3/45	0.22	45	100	Tube
MB2S-E3/80	0.22	80	3000	13" diameter paper tape and reel

RATINGS AND CHARACTERISTICS CURVES ($T_A = 25^\circ\text{C}$ unless otherwise noted)

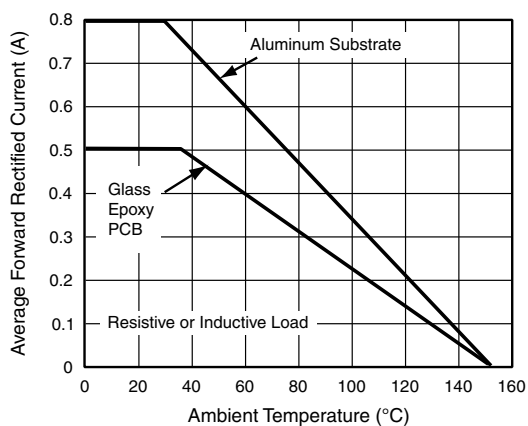


Fig. 1 - Derating Curve for Output Rectified Current

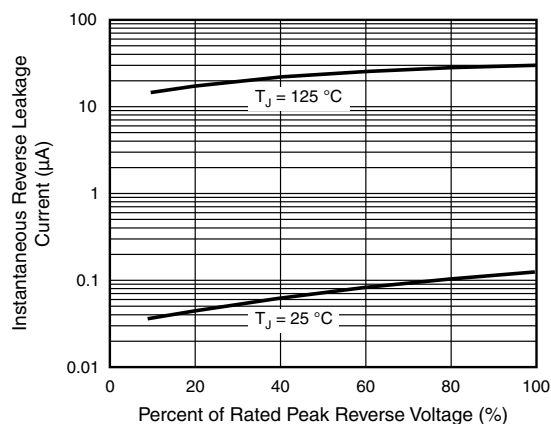


Fig. 4 - Typical Reverse Leakage Characteristics Per Diode

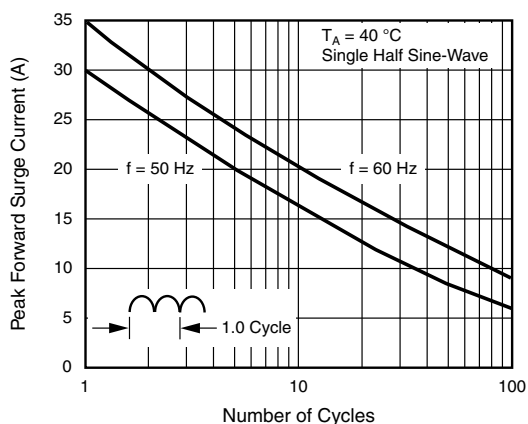


Fig. 2 - Maximum Non-Repetitive Peak Forward Surge Current Per Diode

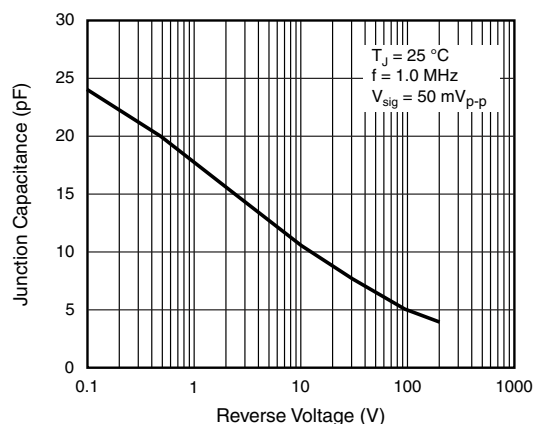


Fig. 5 - Typical Junction Capacitance Per Diode

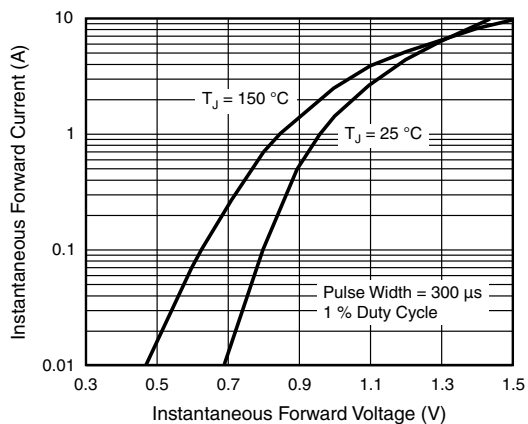
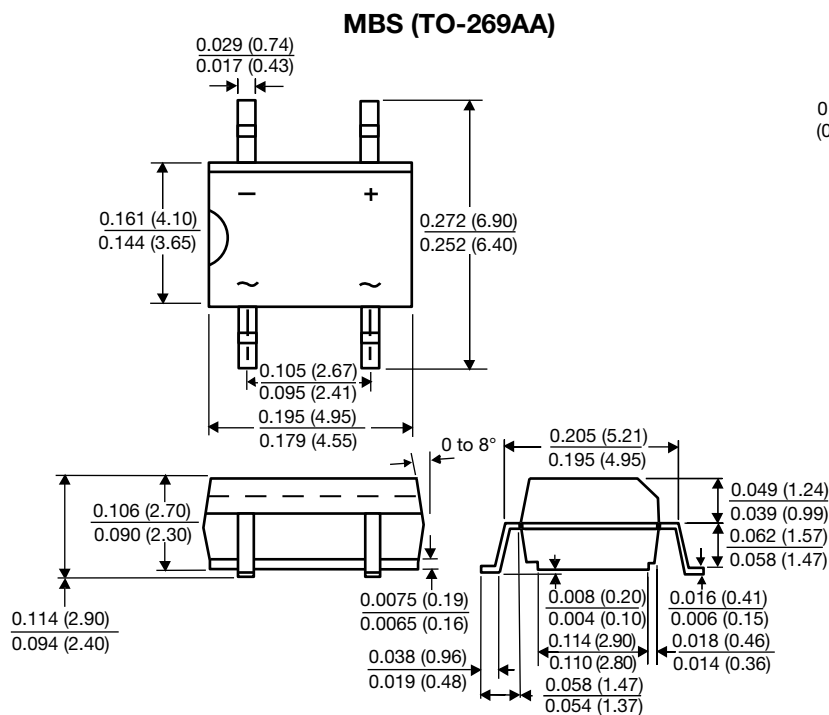


Fig. 3 - Typical Forward Voltage Characteristics Per Diode

PACKAGE OUTLINE DIMENSIONS in inches (millimeters)



Mounting Pad Layout

